

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	6.7mΩ@10V	80A
	8.7mΩ@4.5V	



合肥矽普半导体

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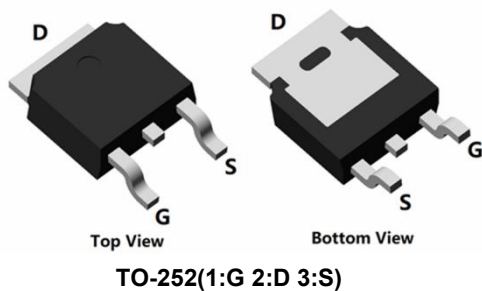
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

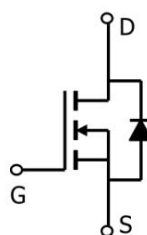
Applications

- Power switching application
- Battery management
- Uninterruptible power supply

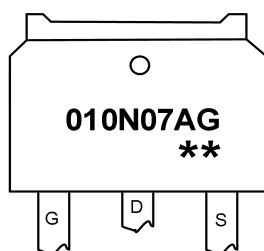
Package



Circuit diagram



Marking



010N07AG : Product code
****** : Week code

Order Information

Device	Package	Unit/Tube
SP010N07AGTH	TO-252	2500

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	80	A
Continuous Drain Current (Tc=100°C)	I_D	55	A
Pulsed Drain Current	I_{DM}	320	A
Single Pulse Avalanche Energy ¹	E_{AS}	272	mJ
Power Dissipation (Tc=25°C)	P_D	100	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.25	°C/W
Storage Temperature Range	T_{STG}	55 to 150	°C
Operating Junction Temperature Range	T_J	55 to 150	°C

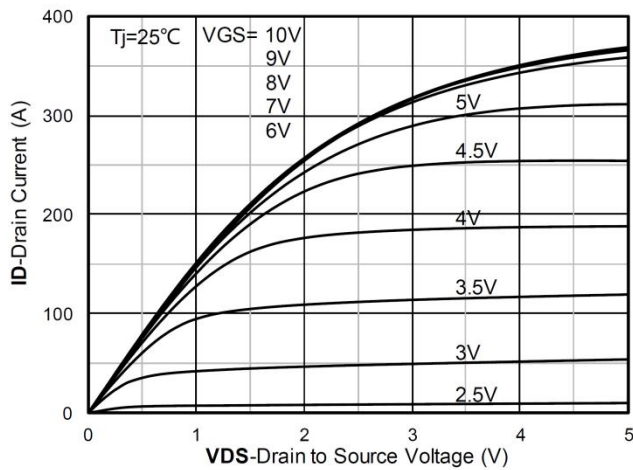
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	B _V DSS	I _D = 250μA, V _{GS} = 0V	100	-	-	V
Drain Cut-Off Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.7	2.5	V
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 30A	-	6.7	8.5	mΩ
		V _{GS} = 4.5V, I _D = 25A	-	8.7	12	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} = 0V, f = 1.0MHz	-	1942	-	pF
Output Capacitance	C _{oss}		-	388	-	
Reverse Transfer Capacitance	C _{rss}		-	12	-	
Total Gate Charge	Q _g	V _{DS} =50V , V _{GS} =10V , I _D =50A	-	67	-	nC
Gate-Source Charge	Q _{gs}		-	12	-	
Gate-Drain Charge	Q _{gd}		-	21	-	
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	V _{GS} = 50V, V _{DS} =50V, I _D =50A R _G = 4.7Ω	-	12	-	nS
Rise Time	t _r		-	11	-	
Turn-Off Delay Time	t _{d(off)}		-	42	-	
Fall Time	t _f		-	6	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =1A , T _J =25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	80	A
Reverse Recovery Time	T _{rr}	I _S =20A, di/dt=100A/us, T _J =25℃	-	59	-	nS
Reverse Recovery Charge	Q _{rr}		-	88	-	nC

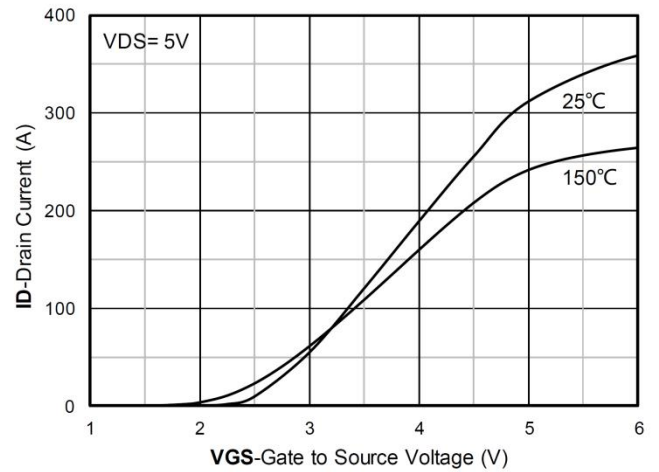
Note:

- The EAS test condition is $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$

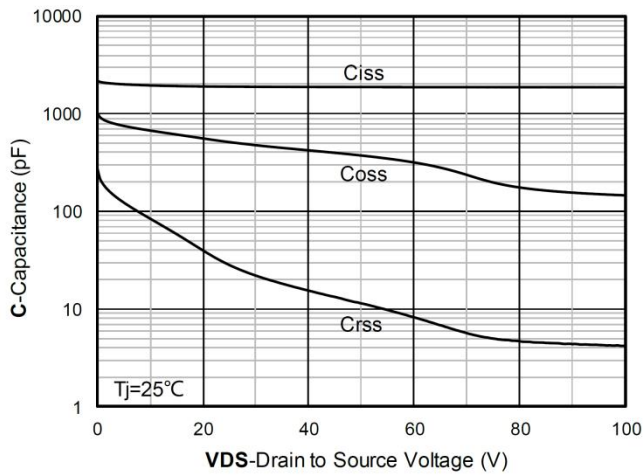
Typical Characteristics



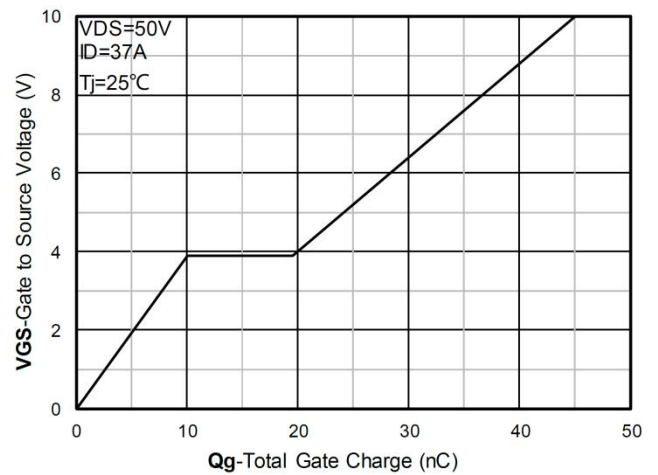
Output Characteristics



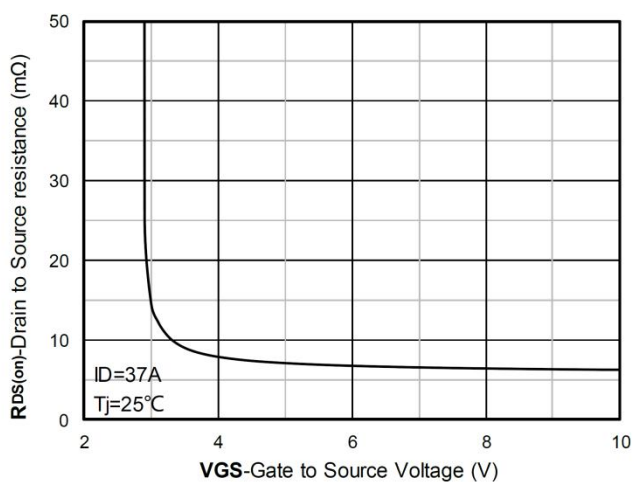
Transfer Characteristics



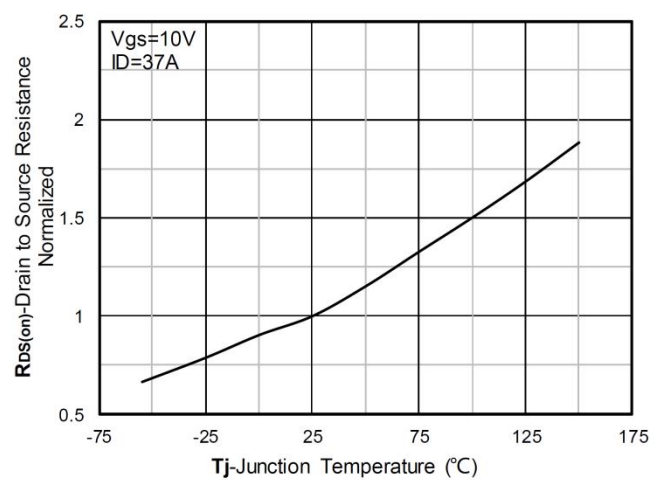
Capacitance Characteristics



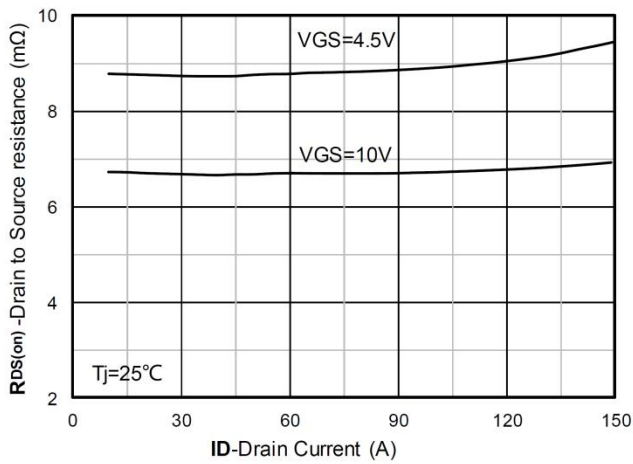
Gate Charge



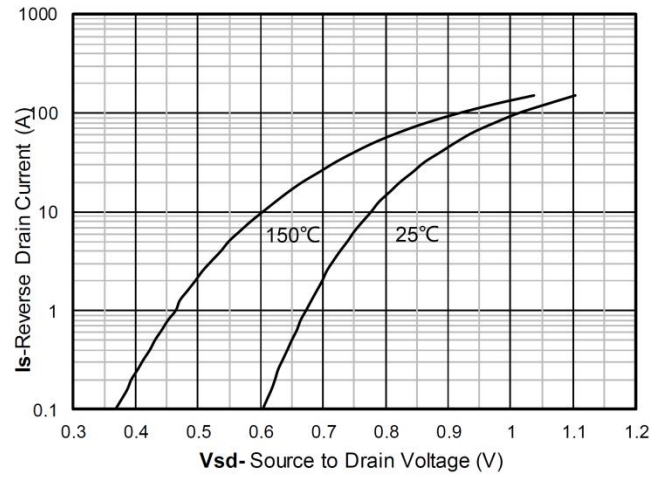
On-Resistance vs Gate to Source Voltage



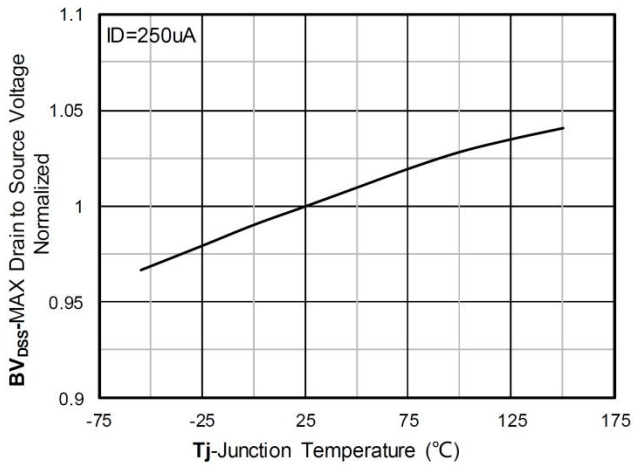
Normalized On-Resistance



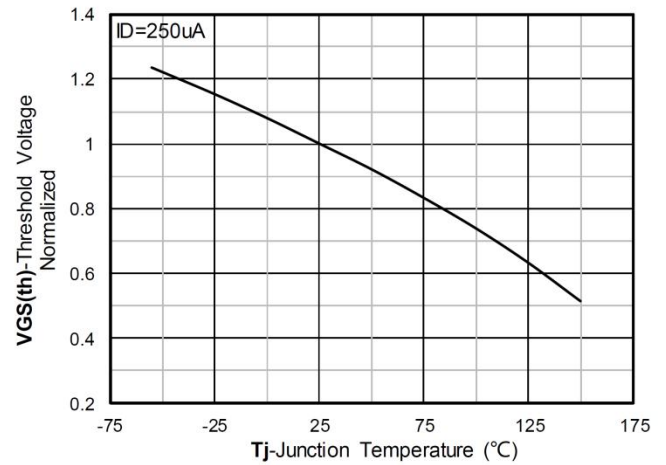
$R_{DS(on)}$ VS Drain Current



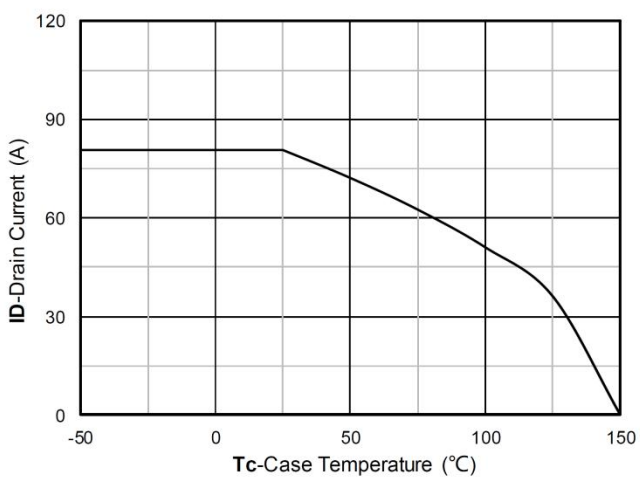
Forward characteristics of reverse diode



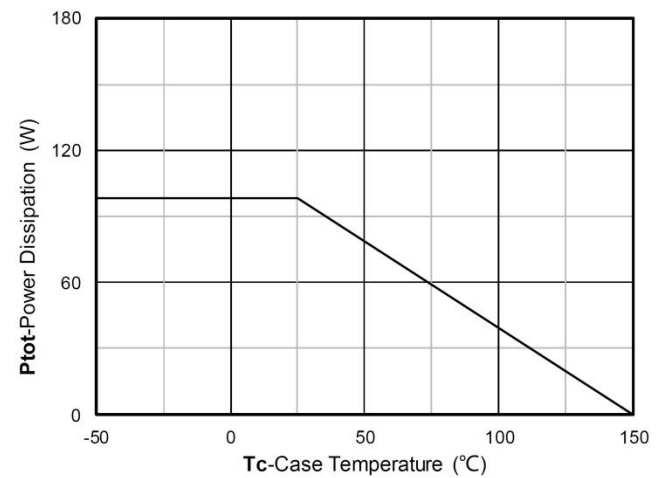
Normalized breakdown voltage



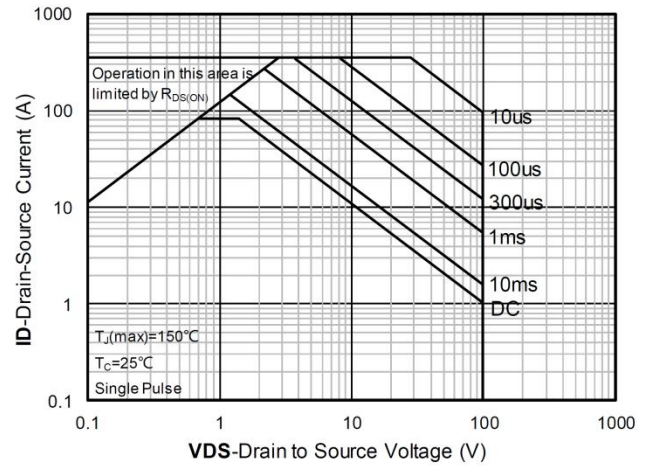
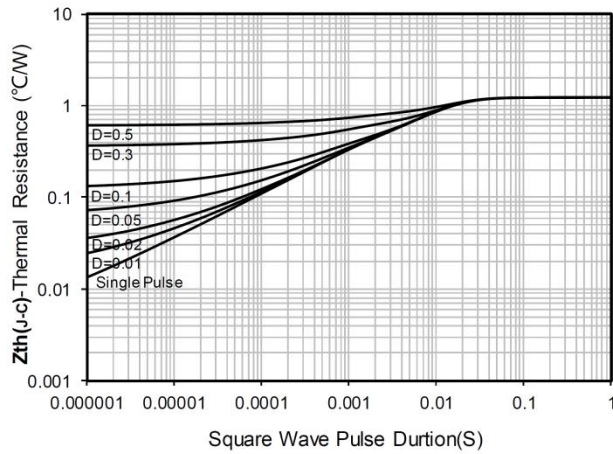
Normalized Threshold voltage

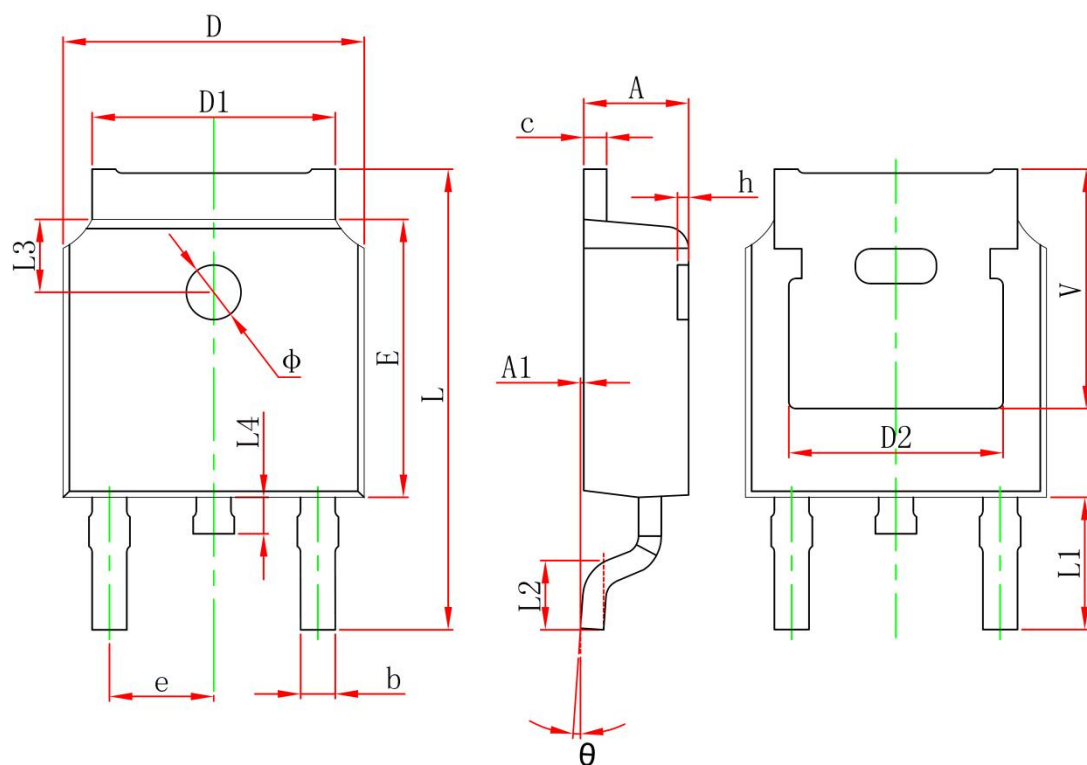


Current dissipation



Power dissipation



TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
ϕ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	